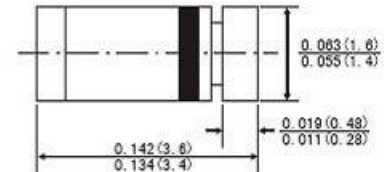




### FEATURES

- Metal-on-silicon junction, majority carrier conduction
- High current capability, low forward voltage drop
- Extremely low reverse current  $I_R$
- Ultra speed switching characteristics
- Small temperature coefficient of forward characteristics
- Satisfactory Wave detection efficiency
- For use in RECORDER | TV | RADIO | TELEPHONE as detectors, super high speed switching circuits, small current rectifier

### Mini-MELF



### MECHANICAL DATA

Dimensions in inches and (millimeters)

- Case: MinMELF glass case (SOD- 80)
- Polarity: color band denotes cathode end
- Weight: Approx. 0.05gram

### ABSOLUTE RATINGS(LIMITING VALUES)

Symbols	Parameters		Value		Units
			LL60	LL60P	
V <sub>RRM</sub>	Repetitive Peak Reverse Voltage		20	30	Volts
I <sub>F</sub>	Forward Continuous Current	T <sub>A</sub> =25°C	30	50	mA
I <sub>FSM</sub>	Peak Forward Surge Current (t=1S)		150	400	mA
T <sub>STG</sub> /T <sub>J</sub>	Storage and junction Temperature Range		-65 to +125		°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering during 10S at 4mm from Case		230		°C

### ELECTRICAL CHARACTERISTICS

Symbols	Parameters	Test Conditions		Value			Units
				Min .	Typ .	Max .	
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> =1mA	LL60	0.35	0.5	Volts	
			LL60P	0.26	0.5		
		I <sub>F</sub> =30mA	LL60	0.70	1.0		
			LL60P	0.70	1.0		
I <sub>R</sub>	Reverse Current	V <sub>R</sub> =15V	LL60	1.0	5.0	μA	
			LL60P	5.0	10.0		
C <sub>J</sub>	Junction Capacitance	V <sub>R</sub> =1V f=1MHz	LL60	4.0		pF	
			LL60P	10.0			
		V <sub>R</sub> =10V f=1MHz	LL60P				
η	Detection Efficiency(See diagram 4)	V <sub>i</sub> =3V f=30MHz C <sub>L</sub> =10pF R <sub>L</sub> =3.8kΩ		60		%	
t <sub>rr</sub>	Reverse Recovery time	I <sub>F</sub> =I <sub>R</sub> =1mA I <sub>TR</sub> =1mA R <sub>C</sub> =100Ω			1	ns	
R <sub>θJA</sub>	Junction Ambient Thermal Resistance	R <sub>JA</sub>		350		°C/W	